

C2 LED Chip Specification

Features:

Growth Technique

MOCVD

Substrate

Sapphire (0001)

Structure

InGaN MQW

Chip size

C2 (375 μ m x 325 μ m)

Wafer thickness

110 $\pm$ 10 μ m

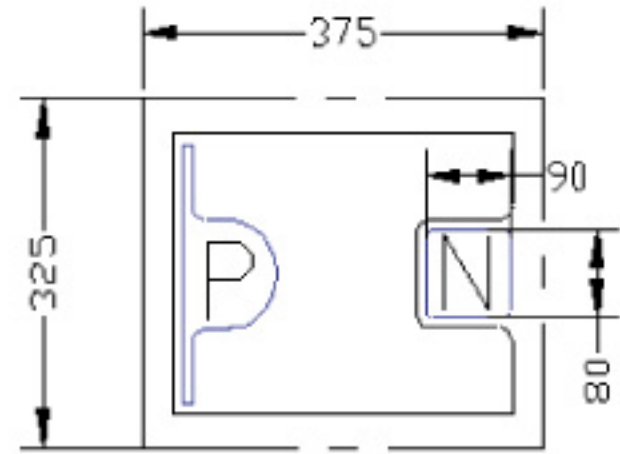
Testing & Sorting

100%

Packaging

19 cm x 19 cm

blue tape medium tack



C2 chip top view (in μ m unit)

Optical and Electrical Characteristics ($T_c = RT, I_f = 20mA, I_r < 2mA$)

Part Number	Dominant wavelength (λ_d , nm)			Forward Voltage (V_f , V)		Radiant Flux (X, mW)				Reverse Voltage (V_r , V)	
	Min	Typ	Max	Typ	Max	B	C	D	E	Min	Typ
LE450-C2-X	445	450	455	3.5	4.0	1.1-2.0	2.0-2.5	2.5-3.0	3.0-3.9	-5	-15
LE460-C2-X	455	460	465	3.5	4.0	1.0-1.7	1.7-2.2	2.2-2.7	2.7-3.5	-5	-15
LE470-C2-X	465	470	475	3.5	4.0	1.0-1.6	1.6-2.0	2.0-2.5	2.5-3.2	-5	-15
LE480-C2-X	475	480	485	3.5	4.0	0.9-1.5	1.5-1.9	1.9-2.3	2.3-2.9	-5	-15
LE495-C2-X	490	495	500	3.5	4.0	0.8-1.3	1.3-1.6	1.6-2.0	2.0-2.6	-5	-15
LE505-C2-X	500	505	510	3.5	4.0	0.7-1.2	1.2-1.5	1.5-1.9	1.9-2.4	-5	-15
LE515-C2-X	510	515	520	3.5	4.0	0.7-1.1	1.1-1.4	1.4-1.8	1.8-2.3	-5	-15
LE525-C2-X	520	525	535	3.5	4.0	0.6-1.0	1.0-1.3	1.3-1.6	1.6-2.1	-5	-15

Mechanical Dimensions

Au bond pad thickness

0.5 μ m – 1.0 μ m

Au bond pad diameter

90 $\pm$ 10 μ m

Application Notes:

1. Recommended optically clear epoxy for die mounting to optimize light output.
2. Assembly processing temperature must not exceed 200°C.
3. GaN LEDs are class 1 ESD sensitive. Please observe appropriate precautions during handling and processing. For further information please see MIL-STD-1686A.

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